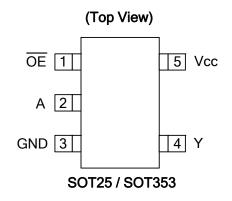


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The 74AHC1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable (\overline{OE}) pin. The device is designed for operation with a power supply range of 2.0V to 5.5V.

Pin Assignments



Features

- Supply Voltage Range from 2.0V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- SOT25 and SOT353: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

Applications

- General Purpose Logic
- Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

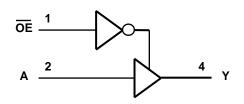


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Pin No.	Description
OE	1	Output Enable
A	2	Data Input
GND	3	Ground
Y	4	Data Output
Vcc	5	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
OE	А	Y
L	Н	Н
L	L	L
Н	Х	Z

74AHC1G125 Document number: DS35176 Rev. 1 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	-20	mA
Ι _{ΟΚ}	Output Clamp Current ($V_O < 0$ or $V_O > V_{CC}$)	±20	mA
Ι _Ο	Continuous output current ($V_0 = 0$ to V_{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	Continuous current through GND	-50	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		2	5.5	V
		$V_{CC} = 2V$	1.5		
VIH	High-level Input Voltage	$V_{CC} = 3V$	2.1		V
		$V_{CC} = 5.5V$	3.85		
		$V_{CC} = 2V$		0.5	
VIL	Low-level input voltage	$V_{CC} = 3V$		0.9	V
		$V_{CC} = 5.5V$		1.65	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 2V$		-50	uA
I _{OH}	High-level output current	$V_{CC} = 3.3V \pm 0.3V$		-4	
		$V_{CC} = 5V \pm 0.5V$		-8	- mA
		$V_{CC} = 2V$		50	uA
I _{OL}	Low-level output current	$V_{CC} = 5V \pm 0.5V$		4	
		$V_{CC} = 3V$		8	- mA
A ± / A \ /	Input transition rise or fall	$V_{CC} = 3.3V \pm 0.3V$		100	
Δt/ΔV	rate	$V_{CC} = 5V \pm 0.5V$		20	ns/V
T _A	Operating free-air temperature		-40	125	٥C

Notes: 3. Unused inputs should be held at V_CC or Ground.





SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Electrical Characteristics

		T (0)			25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	
Symbol	Parameter	Test Conditions	V _{cc}	Min	Тур.	Max	Min	Max	Min	Max	Unit
			2V	1.9	2		1.9		1.9		
		Ι _{ΟΗ} = -50μΑ	3V	2.9	3		2.9		2.9		
V _{OH}	High Level		4.5V	4.4	4.5		4.4		4.4		V
0.11	Output Voltage	I _{OH} = -4mA	3V	2.58			2.48		2.40		
		I _{OH} = -8mA	4.5V	3.94			3.8		3.70		
			2V			0.1		0.1		0.1	
		I _{OL} = 50μΑ	3V			0.1		0.1		0.1	
V _{OL}	Low Level		4.5V			0.1		0.1		0.1	V
	Output Voltage	$I_{OL} = 4mA$	3V			0.36		0.44		0.55	ļ
		I _{OL} = 8mA	4.5V			0.36		0.44		0.55	
lı –	Input Current	$V_1 = 5.5V$ or GND	0 to 5.5V			± 0.1		± 1		±2	μA
I _{OZ}	Z State Leakage Current	V _O =0 to 5.5V	5.5V			0.25		2.5		10	μA
I _{CC}	Supply Current	$V_I = 5.5V \text{ or GND}$ $I_O=0$	5.5V			1		10		40	μΑ
C _i	Input Capacitance	V _I = V _{CC} – or GND	5.5V		2.0	10		10		10	pF
θ _{JA}	Thermal Resistance SOT25	SOT25	(Note 4)		195						°C/W
UJA	Junction-to- Ambient	SOT353	(10010-4)		430						C/ W
0	Thermal Resistance	SOT25	(Note 4)		58						°C/W
θ _{JC}	Junction-to- Case	SOT353	(Note 4)		155						C/VV

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

V_{CC} = 3.3V ± 0.3 (see Figure 1)

Parameter	From	то			25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	Unit
Parameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	^	V	C _L =15pF	0.6	4.7	8.0	0.6	9.5	0.6	11.5	ns
t _{pd}	A	ř	C _L =50pF	0.6	6.6	11.5	0.6	13.0	0.6	14.5	ns
		V	C _L =15pF	0.6	5.0	8.0	0.6	9.5	0.6	10.5	ns
t _{en}	OE	ř	$C_L=50pF$	0.6	6.9	11.5	0.6	13.0	0.6	14.5	ns
		V	C _L =15pF	0.6	6.0	9.7	0.6	11.5	0.6	12.5	ns
t _{dis}	OE	ř	C _L =50pF	0.6	8.3	13.2	0.6	15.0	0.6	16.5	ns

$V_{CC} = 5V \pm 0.5V$ (see Figure 1)

Deremeter	From	то			25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	Unit
Parameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	А	V	C _L =15pF	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns
t _{pd}	A	ř	C _L =50pF	0.6	4.8	7.5	0.6	8.5	0.6	9.5	ns
		V	C _L =15pF	0.6	3.6	5.1	0.6	6.0	0.6	6.5	ns
t _{en}	OE	ř	C _L =50pF	0.6	6.5	11.4	0.6	13.0	0.6	14.5	ns
	ŌĒ	V	C _L =15pF	0.6	4.1	6.8	0.6	8.0	0.6	8.5	ns
t _{dis}	ÛE	ř	C _L =50pF	0.6	5.7	8.8	0.6	10.0	0.6	11.0	ns

Operating Characteristics

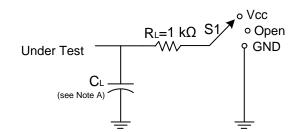
T_A = 25 °C

	Parameter	Test Conditions	V _{CC} = 5 V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 1 MHz No Load	12	pF



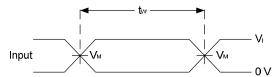
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

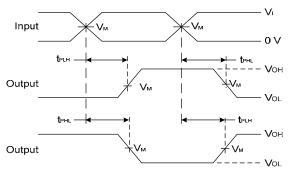


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

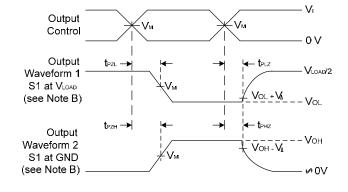
N N	Inputs		V	0	V۵
V _{CC}	VI	t _r /t _f	V _M	CL	VΔ
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 1 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}

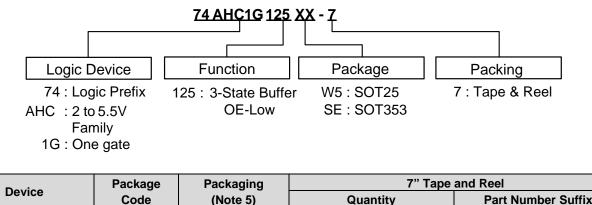
E. t_{PZL} and t_{PZH} are the same as t_{EN.}

F. t_{PLH} and t_{PHL} are the same as $t_{\mathsf{PD.}}$



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

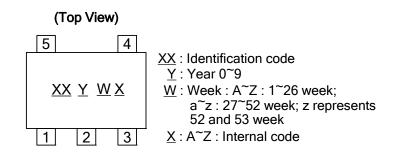
Ordering Information



	Device	i donago	i ackagnig	1 1000	
	Device	Code	(Note 5)	Quantity	Part Number Suffix
B ,	74AHC1G125W5-7	W5	SOT25	3000/Tape & Reel	-7
B	74AHC1G125SE-7	SE	SOT353	3000/Tape & Reel	-7

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



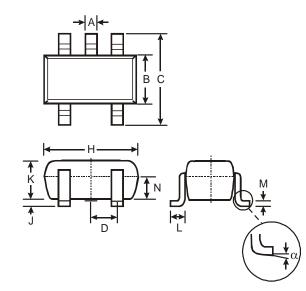
Part Number	Package	Identification Code
74AHC1G125W5	SOT25	ΥY
74AHC1G125SE	SOT353	ΥY



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

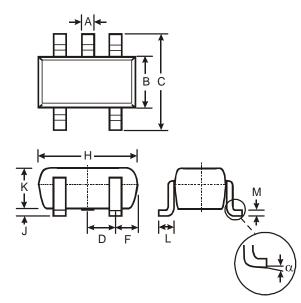
Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



SOT25				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
в	1.50	1.70	1.60	
С	2.70	3.00	2.80	
D		_	0.95	
Н	2.90	3.10	3.00	
ر	0.013	0.10	0.05	
Κ	1.00	1.30	1.10	
┙	0.35	0.55	0.40	
Μ	0.10	0.20	0.15	
Ν	0.70	0.80	0.75	
α	0°	8°		
All Dimensions in mm				

(2) Package Type: SOT353



SOT353				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
κ	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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